

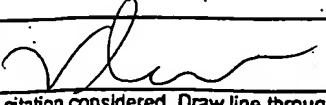
Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. <b>10559-584002</b>	Application No.
<b>Information Disclosure Statement</b> by Applicant (Use several sheets if necessary)  (37 CFR §1.98(b))		Applicant <b>Chris E. Barns et al.</b>	
		Filing Date <b>March 12, 2004</b>	Group Art Unit

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						

Foreign Patent Documents or Published Foreign Patent Applications							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation
							Yes No
	AB						

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
LV	AC	Ducroquet et al., "Full CMP Integration...", IEEE Transactions on Electron Devices, 48(8):1816-1821, 2001
	AD	Matsuda et al., "Performance Improvement of Metal...", Symposium on VLSI Technology Digest of Technical Papers, 2001
	AE	Ushiki et al., "Reliable Tantalum-Gate...", IEEE Transactions on Electron Devices, 44(9):1467-1472, 1997
	AF	Yagishita et al., "Improvement of Threshold Voltage...", IEEE Transactions on Electron Devices, 48(8):1604-1611, 2001
	AG	Planar Solutions Announces New Second Step Copper CMP Slurry," Arch SemiConductor Photopolymers: About Us
	AH	Conaghan et al., "Applications of silicides in semiconductor processing,"
	AI	Abstract, Cabot Microelectronics Corporation, Semiconductor Products, 2000
LV	AJ	Abstract, Cabot Microelectronics Corporation, FAX (Frequently Asked Questions), 2000

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Examiner Signature 	Date Considered <i>10/11/05</i>
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	